

IN THE SPECIFICATION:

Please replace paragraph [0046] with the following amended paragraph:

[0046] For example, as illustrated in FIG. 7, the level of an internally generated voltage used to bias the substrates of cell transistors 224 of a memory device 700 200, commonly referred to as back-bias voltage (V_{BB}), may be varied by a temperature controlled V_{BB} generator 240 (which may be used separately or in conjunction with a temperature controlled V_{BB} generator 230). Lowering V_{BB} as temperature of the device 700 200 increases may improve (lower) refresh time by increasing cell threshold voltage via body effect. V_{BB} is typically negative with respect to a reference ground. As such, the V_{BB} generator 240 may include components similar to those of the V_{PP} generator 230 described above.